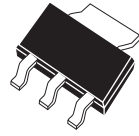


**CZTA77**  
**SURFACE MOUNT**  
**PNP SILICON**  
**DARLINGTON TRANSISTOR**



**SOT-223 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CZTA77 type is a Silicon PNP Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

**MARKING CODE: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

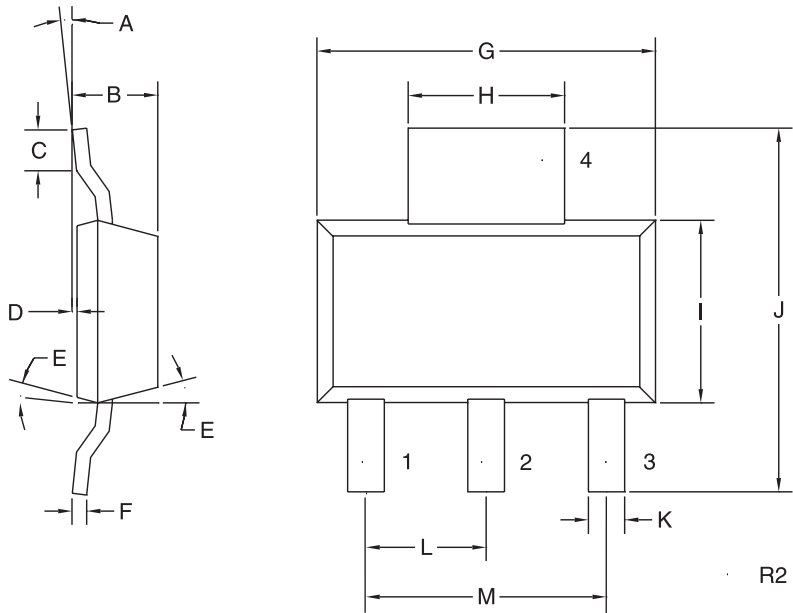
	<b>SYMBOL</b>		<b>UNITS</b>
Collector-Emitter Voltage	$V_{CES}$	60	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Collector Current	$I_C$	1.0	A
Power Dissipation	$P_D$	2.0	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	°C
Thermal Resistance	$\theta_{JA}$	62.5	°C/W

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{CES}$	$V_{CE}=50V$		500	nA
$I_{CBO}$	$V_{CB}=50V$		100	nA
$I_{EBO}$	$V_{EB}=10V$		100	nA
$BV_{CES}$	$I_C=100\mu A$	60		V
$BV_{CBO}$	$I_C=100\mu A$	60		V
$V_{CE(SAT)}$	$I_C=100mA, I_B=0.1mA$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0V, I_C=100mA$		2.0	V
$h_{FE}$	$V_{CE}=5.0V, I_C=10mA$	10,000		
$h_{FE}$	$V_{CE}=5.0V, I_C=100mA$	10,000		
$f_T$	$V_{CE}=5.0V, I_C=10mA, f=100MHz$	125		MHz

R3 (14-November 2002)

**SOT-223 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

**MARKING CODE:  
FULL PART NUMBER**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	7°	0°	7°
B	0.063	0.067	1.60	1.70
C	0.022		0.55	
D	0.001	0.004	0.03	0.10
E	15°		15°	
F	0.009	0.013	0.23	0.33
G	0.248	0.264	6.30	6.71
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.71
J	0.264	0.287	6.71	7.29
K	0.024	0.031	0.61	0.79
L	0.091		2.31	
M	0.181		4.60	

SOT-223 (REV: R2)

R3 (14-November 2002)